

CLAIMS

What is claimed is:

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1. ~~A method comprising:~~
introducing a dielectric layer over a substrate
between an interconnection line and a contact point on the
substrate, the dielectric layer comprising a plurality of
different material layers; and
patterning an interconnection to the contact point.

2. The method of claim 1, wherein patterning an
interconnection to the contact point comprises patterning
an interconnection directly to a device on the substrate.

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3. ~~The method of claim 2, wherein introducing the~~
dielectric layer comprises introducing a plurality of
alternating material layers.

4. ~~The method of claim 3, wherein the introducing the~~
dielectric layer comprises introducing silicon dioxide as
the ultimate layer.

5. The method of claim 4, wherein introducing a
plurality of alternating material layers comprises
alternating silicon dioxide layers with at least one other
material layers.

6. The method of claim 5, wherein the number of
alternating silicon dioxide layers comprises at least six.

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7. ~~The method of claim 1, wherein the dielectric layer~~
comprises a first dielectric layer, the method further

comprising introducing a second dielectric layer between the first dielectric layer and the etch stop layer.

8. A method comprising:

introducing a dielectric layer over a substrate between an interconnection line and the substrate, the dielectric layer comprising a plurality of alternating material layers; and

patterning an interconnection to the substrate.

9. The method of claim 8, wherein the interconnection line comprises a first level interconnection line.

10. The method of claim 9, wherein introducing a plurality of alternating material layers comprises introducing silicon dioxide as the ultimate material layer.

11. The method of claim 10, wherein introducing a plurality of alternating material layers comprises alternating silicon dioxide layers with at least one other material layers.

12. The method of claim 11, wherein the number of alternating silicon dioxide layers comprises at least six.

13. The method of claim 8, wherein the dielectric layer comprises a first dielectric layer, the method further comprising introducing a second dielectric layer between the first dielectric layer and the substrate.

14. An apparatus comprising:
a substrate comprising a plurality of devices formed thereon; and

an interlayer dielectric layer comprising a base layer and a cap layer, the cap layer comprising a plurality of alternating material layers overlying the substrate.

15. The apparatus of claim 14, wherein the cap layer comprises silicon dioxide as the ultimate material layer.

16. The apparatus of claim 14, wherein the cap layer comprises a plurality of silicon dioxide layers alternated with at least one other material layers.

17. The apparatus of claim 16, wherein the number of alternating silicon dioxide layers comprises at least six.

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